

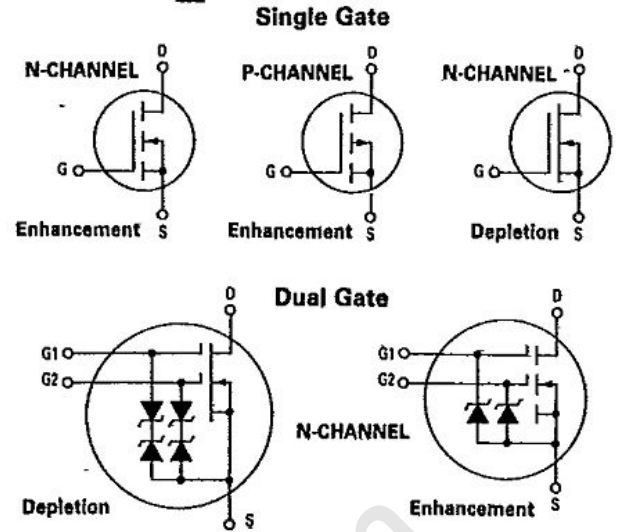
# MOSFETs

T-91-60

MOSFETs are available in either depletion/enhancement or enhancement mode (in general, depletion/enhancement devices are operated in the depletion mode and are referred to as depletion devices). They are available in both N- and P-channel, and both single gate and dual gate construction. Some MOSFETs are also offered with input diode protection which reduces the chance of damage from static charge in handling.

**Table 4. Dual Gate**

These devices are especially suited for RF amplifier and mixer applications in TV tuners, radio, etc. The Dual Gate construction also allows easy AGC control with very low power.



## N-Channel MOSFETs

Package TO-	Device	$R_e   Y_{fs}  $		$R_e   Y_{os}  $		$C_{iss}$	$C_{rss}$	NF		$V_{(BR)GSS}$ $V_{(BR)GDO}$	$V_{GS(off)}$		$I_{DSS}$	
		(mmho) Min	@ f (MHz)	( $\mu$ mho) Max	@ f (MHz)			(dB) Max	@ RG = 1K f (MHz)		(V) Min	Min	Max	Min
72	MFE521	10	0.001	—	—	4.0	0.02	3.5	200	10	0.5	2.0	5.0	20
72	MFE211	17	0.001	—	—	—	0.05	3.5	200	$\pm 6.0$	-0.2	-5.5	6.0	40
72	MFE212	17	0.001	—	—	—	0.05	4.0	45	$\pm 6.0$	-0.2	-5.5	6.0	40
72	MFE203	7.0	0.001	—	—	4.3 <sup>t</sup>	0.03	4.5	200	$\pm 6.0$	-0.2	-5.0	3.0	11
72	MFE201	8.0	0.001	—	—	4.5 <sup>t</sup>	0.03	4.5	200	$\pm 6.0$	-0.2	-5.0	6.0	30
72	MFE202	8.0	0.001	—	—	4.3 <sup>t</sup>	0.03	4.5	200	$\pm 6.0$	-0.2	-5.0	6.0	30
72	MFE120	8.0	0.001	—	—	7.0	0.023	5.0	105	$\pm 7.0$	—	-4.0	2.0	18
72	MFE121	10	0.001	—	—	6.0	0.023	5.0	60	$\pm 7.0$	—	-4.0	5.0	30
72	MFE122	8.0	0.001	—	—	7.0	0.023	5.0	200	$\pm 7.0$	—	-4.0	2.0	20
72	MFE131	8.0	0.001	—	—	7.0	0.05	5.0	200	$\pm 7.0$	—	-4.0	3.0	30
72	MFE204	10	0.001	—	—	—	0.03	5.0	400	25	-0.2	-4.0	6.0	30
72	MFE130	8.0	0.001	—	—	7.0	0.05	5.0	105	$\pm 7.0$	—	-4.0	3.0	30
72	MFE209	10	0.001	—	—	7.0	0.03	6.0	500	$\pm 7.0$	-0.1	-4.0	5.0	30
72	MFE131	8.0	0.001	—	—	7.0	0.05	5.0	100	$\pm 7.0$	—	-4.0	3.0	30

<sup>t</sup> = typical